



An ILD vertex detector with CMOS sensors - status report

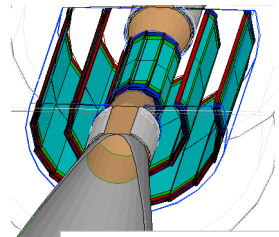
J. Baudot, for the IPHC group
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Orsay 2011 May 23



- x Detector specifications
- x CMOS sensor architecture
- x Perspective toward the DBD
- x Beyond the DBD
- x Summary
- x Back-up slides

The CMOS sensor-based VXD



● Inner layer – internal side

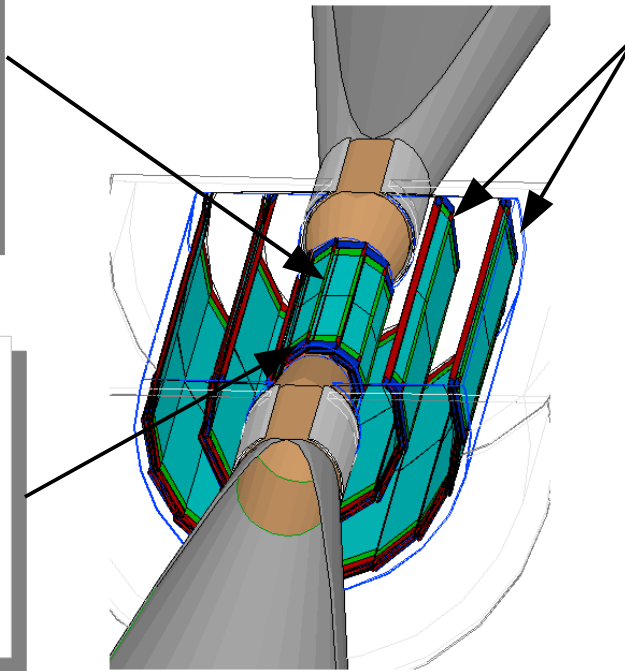
- x Optimized for resolution
- x $16 \times 16 \mu\text{m}^2$
- x Q encoding: binary
- x $t_{\text{Integration}} \sim 40 \mu\text{s}$
- x Sensitive area $\sim 2 \text{ cm}^2$

● Inner layer – external side

- x Optimized for r.o. speed
- x $16 \times 64 \mu\text{m}^2$
- x Q encoding: binary
- x $t_{\text{Integration}} \sim 10 \mu\text{s}$
- x Sensitive area $\sim 2 \text{ cm}^2$

● Outer layer

- x Optimized for low power
- x $35 \times 35 \mu\text{m}^2$
- x Q encoding: 4-bits
- x $t_{\text{Integration}} \sim 100 \mu\text{s}$
- x Sensitive area $\sim 4 \text{ cm}^2$



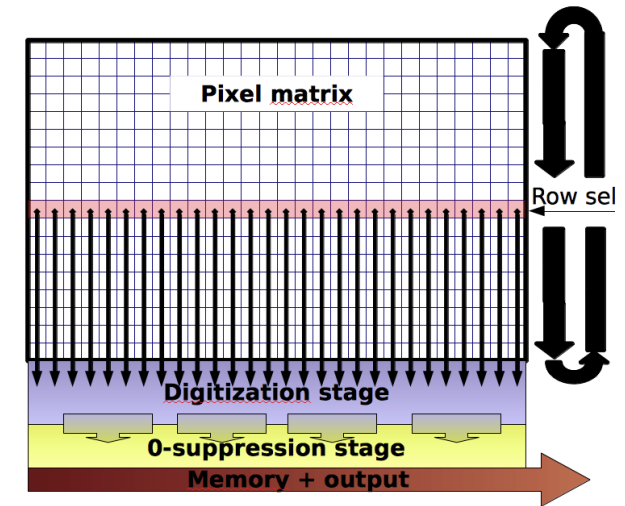
layer	radius (mm)	length (mm)	# ladders	# sensors*	#.10 ⁶ pixels	t_{int} (μs)	$\sigma_{\text{s.p.}}$ (μm)
1	16/18	125	14	168	66 + 16	40 / 10	< 3 / ~5
2	37/39	250	26	312	2x112	100	< 4
3	58/60	250	40	480	2x173	100	< 4
total			80	960	652		

* Numbers corresponding to current CMOS technology (0.35 μm) prototypes

Architecture concepts

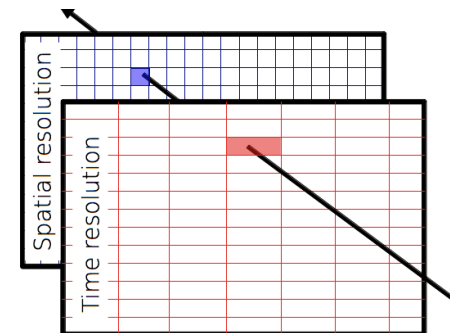
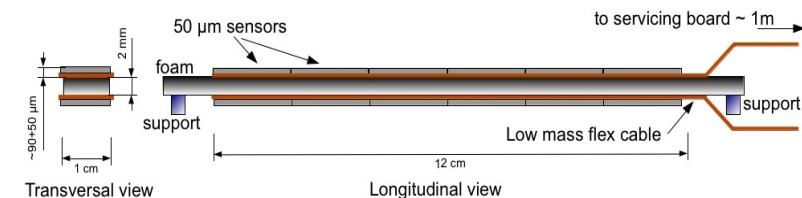
● CMOS sensors: high granularity & low power

- x In-pixel: pre-amplification pedestal suppression
- x periphery: digitization + zero-suppression
- x Readout strategy = rolling-shutter (column //)
 - single row active at a time → save power
 - $t_{\text{integration}} = t_{\text{read-out}}$
- x Active only during train (2 to 4 ms)
 - Power pulsing with duty cycle 1/100 to 1/50
- x Collaboration: IPHC, IRFU

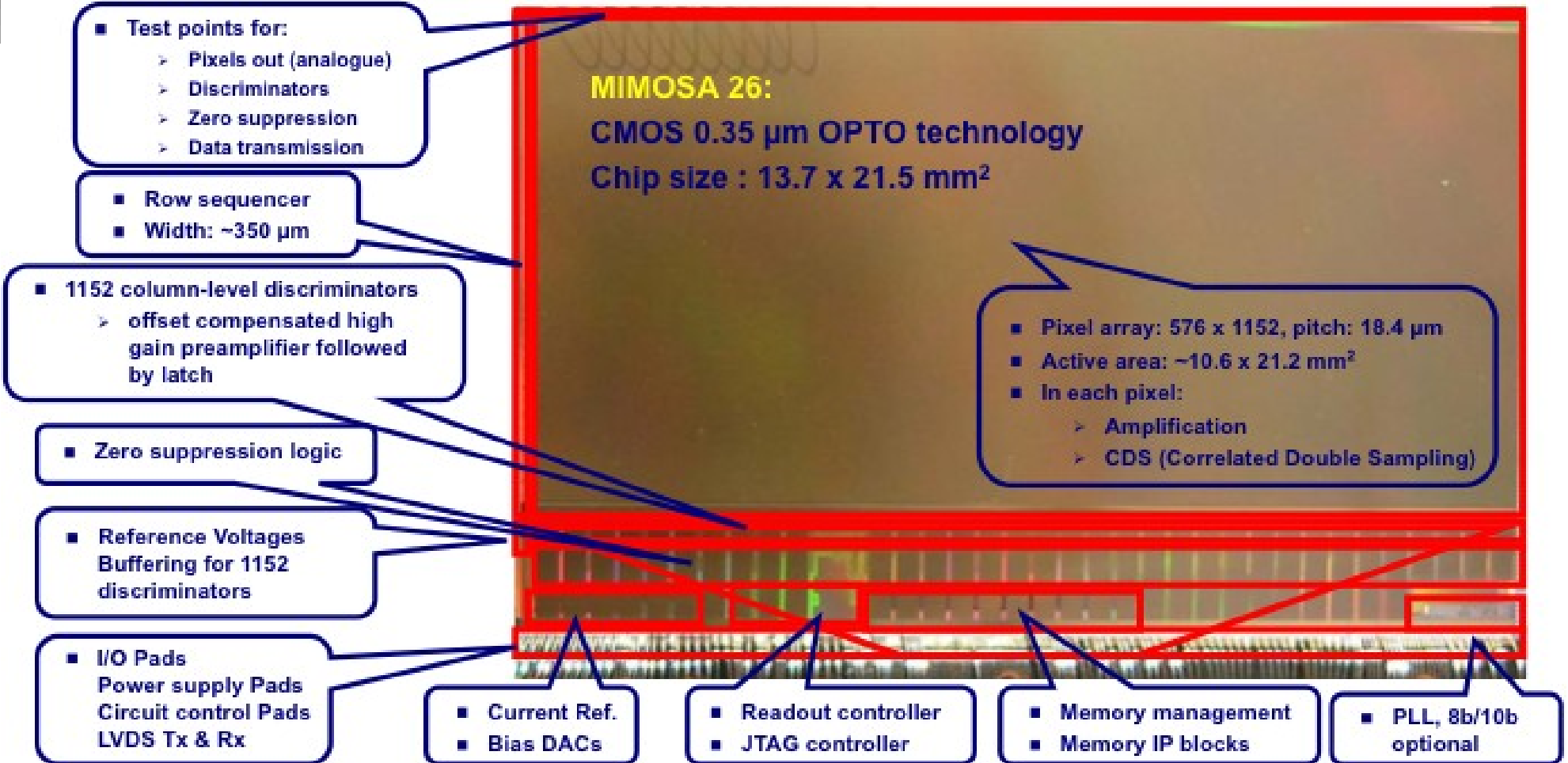
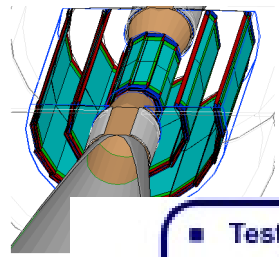


● Ladders:

- x Sandwich: sensor+cable / stiffener / cable+sensor
 - Increased stiffness → low mass spacer (foam)
 - Allows to combine sensors with different spec.
- x Air cooling assumed
- x PLUME collaboration:
 - DESY, IPHC, Uni. Bristol, Uni. Oxford

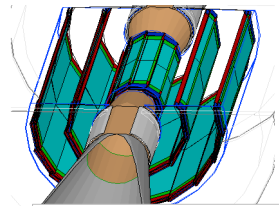


CMOS sensor prototypes



- x EUDET Final Telescope chip
- x Fabricated in 2009 & 2010 with standard (few $\Omega\cdot\text{cm}$) & high resistivity (400 $\Omega\cdot\text{cm}$)
- x Yield 75% for "perfect" sensors, 90% for usable
- x Thinned down to 50 μm

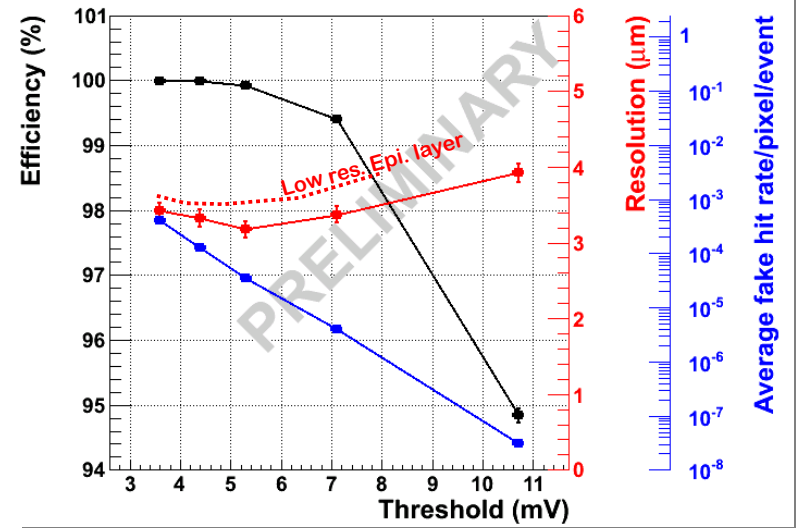
CMOS sensor prototypes



MIMOSA 26

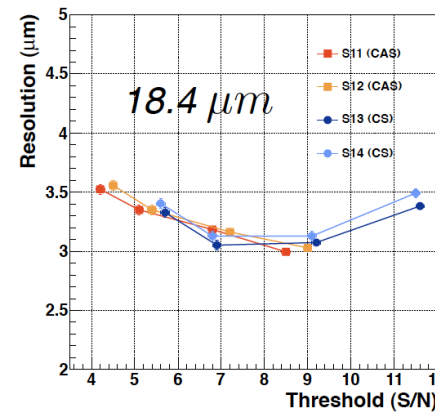
- x Readout time (pixel clock 80 MHz) $\sim 100 \mu\text{s}$
 - $\rightarrow > 10^6 \text{ part/cm}^2/\text{s}$
- x Power dissipated $\sim 250 \text{ mW/cm}^2$

Mi-26 HR-10, non irradiated

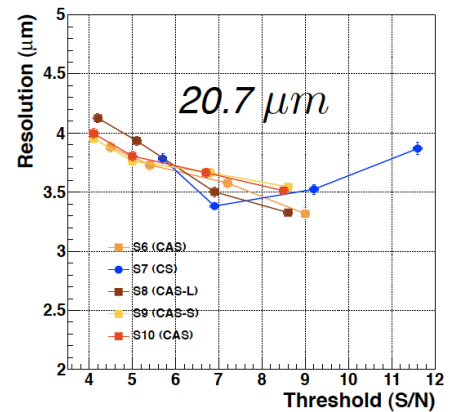


MIMOSA 22 High Resistivity (400 Ω.cm), fab 2010

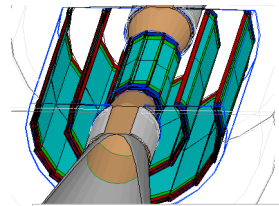
Resolution vs Threshold



Resolution vs Threshold



CMOS sensor prototypes



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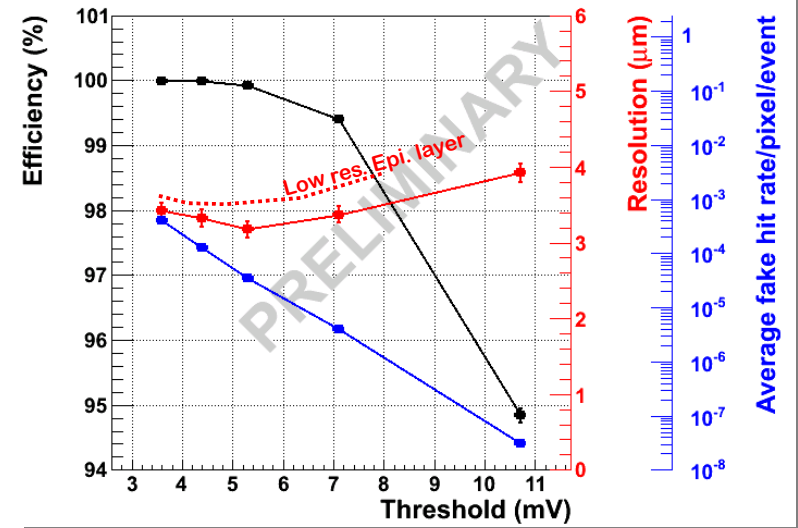
Spatial resolution ($\sigma_{\text{s.p.}}$)

- x Depends on: pitch, epi. layer, SNR, q-encoding
- x Extrapolation from previous measurements

Pitch (μm)	20.7	18.4	16
Nb of bits	1	1	1
Epi. layer	high R.	high R.	high R.
	measured	measured	extrapolated
$\sigma_{\text{s.p.}}$ (μm)	3.5	3.1	2.7

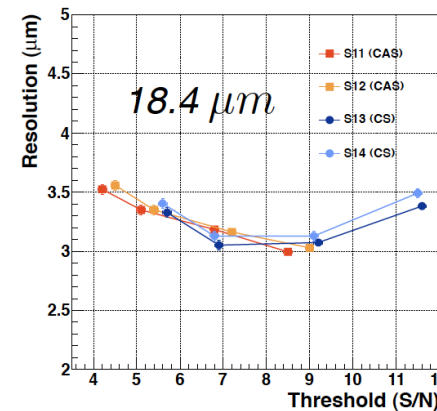
Pitch (μm)	20	20	30	35	40
Nb of bits	12	4	12	4	12
Epi. layer	low R.	low R.	low R.	high R.	low R.
	measured	re-processed	measured	extrapolated	measured
$\sigma_{\text{s.p.}}$ (μm)	1.5	1.7	2.1	< 4	3

Mi-26 HR-10, non irradiated

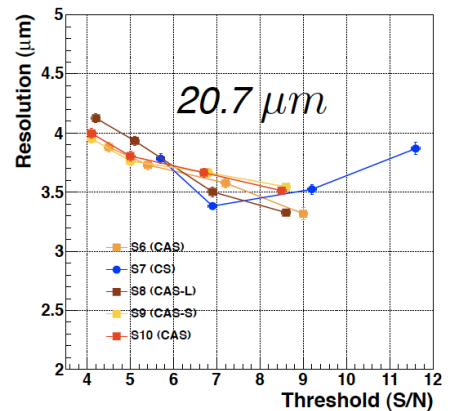


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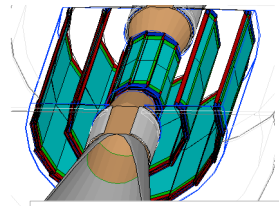
Resolution vs Threshold



Resolution vs Threshold

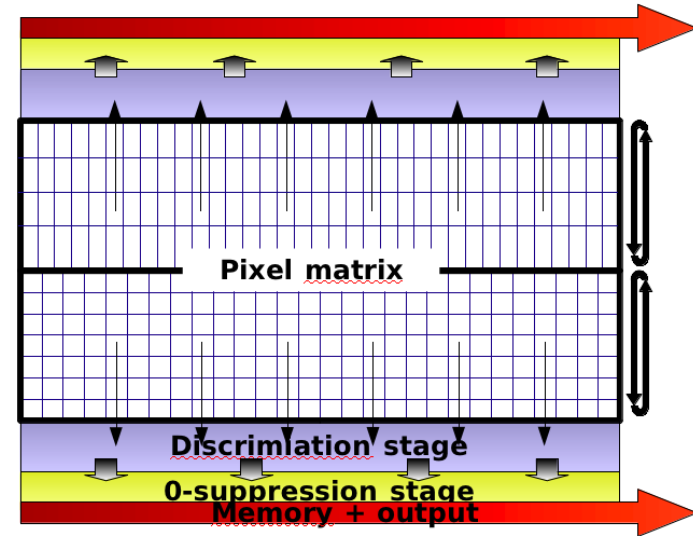


DBD perspective: sensors



● Inner layer sensors

- x MIMOSA 30
- x **Two-sided readout**
 - 256 rows with pitch $16 \times 16 \mu\text{m}^2$
 - Spatial resolution $< 3 \mu\text{m}$
 - 64 rows with pitch $16 \times 64 \mu\text{m}^2$
 - Spatial resolution $\sim 5 \mu\text{m}$
- x 128 columns with binary output
 - with pixel clock @ 100 MHz
 - Readout time $< 50 \mu\text{s}$



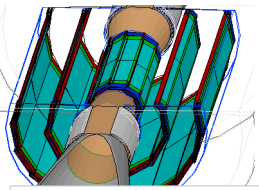
● Outer layers sensor

- x MIMOSA 31
- x Pitch $35 \times 35 \mu\text{m}^2$ & **4-bits output**
 - Spatial resolution $< 4 \mu\text{m}$
- x 48 columns over 64 rows
 - Readout time $\leq 100 \mu\text{s}$

● For both sensors

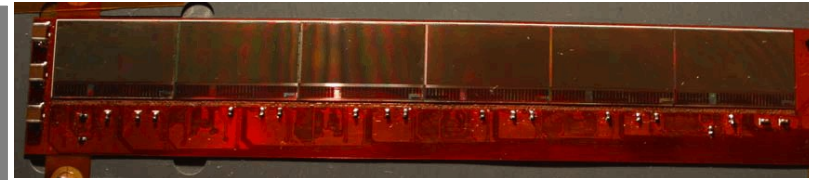
- x CMOS $0.35 \mu\text{m}$ technology
- x fabrication Q4 2011 (if funding available)
- x Beam test before mid-2012
 - Translation into $0.18 \mu\text{m}$ techno. underway

DBD perspective: ladders

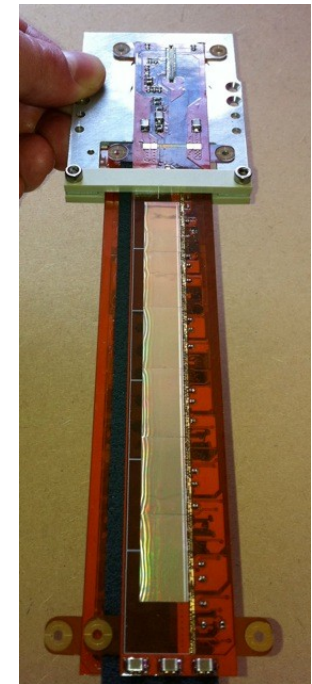


● PLUME ladder 2010 design

- x Focus on functionality (8 Mpixels, 9 W cont. readout 100 μ s)
- x Material budget $\sim 0.6\%$ X0 (= 2x target value)
 - low-mass cable very wide & uses copper traces
 - Stiffener SiC foam with 8% density
- x Lab tests
 - Air cooling @ 2 m/s
 - Positioning precision + stability (ongoing)
 - Crude power pulsing test (MIMOSA 26 not optimized)
- x Beam test : November 2011
 - Impact on resolution from air cooling & power pulsing

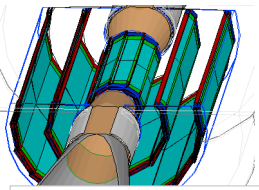


Thermal measurement



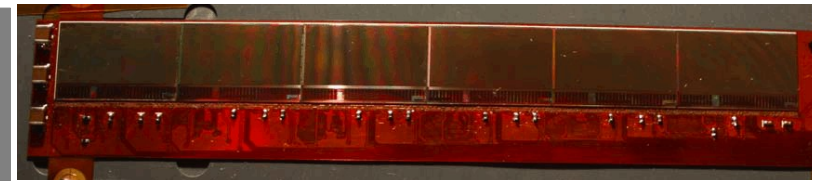
Mechanical prototype with dummy (smaller) sensors

DBD perspective: ladders



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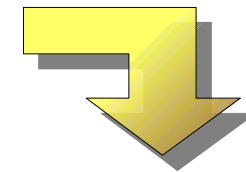


Thermal measurement



● PLUME ladder 2011 design

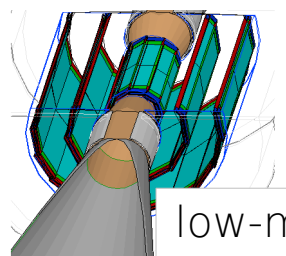
- x Optimized for material budget
 - Final figure depends on cable mass & stiffener (design finalized Spring'10) assuming 13 μ m aluminum traces & 4% SiC foam
 - **Transversal cross-section $\sim 0.29\%$ of X0**
 - **Average over the ladder surface (weight/sensitive area) $\sim 0.47\%$ of X0**
- x New low-mass cable fabrication Summer 2011
 - First ladder \sim fall 2011, Beam test summer 2012



Extrapolation with:

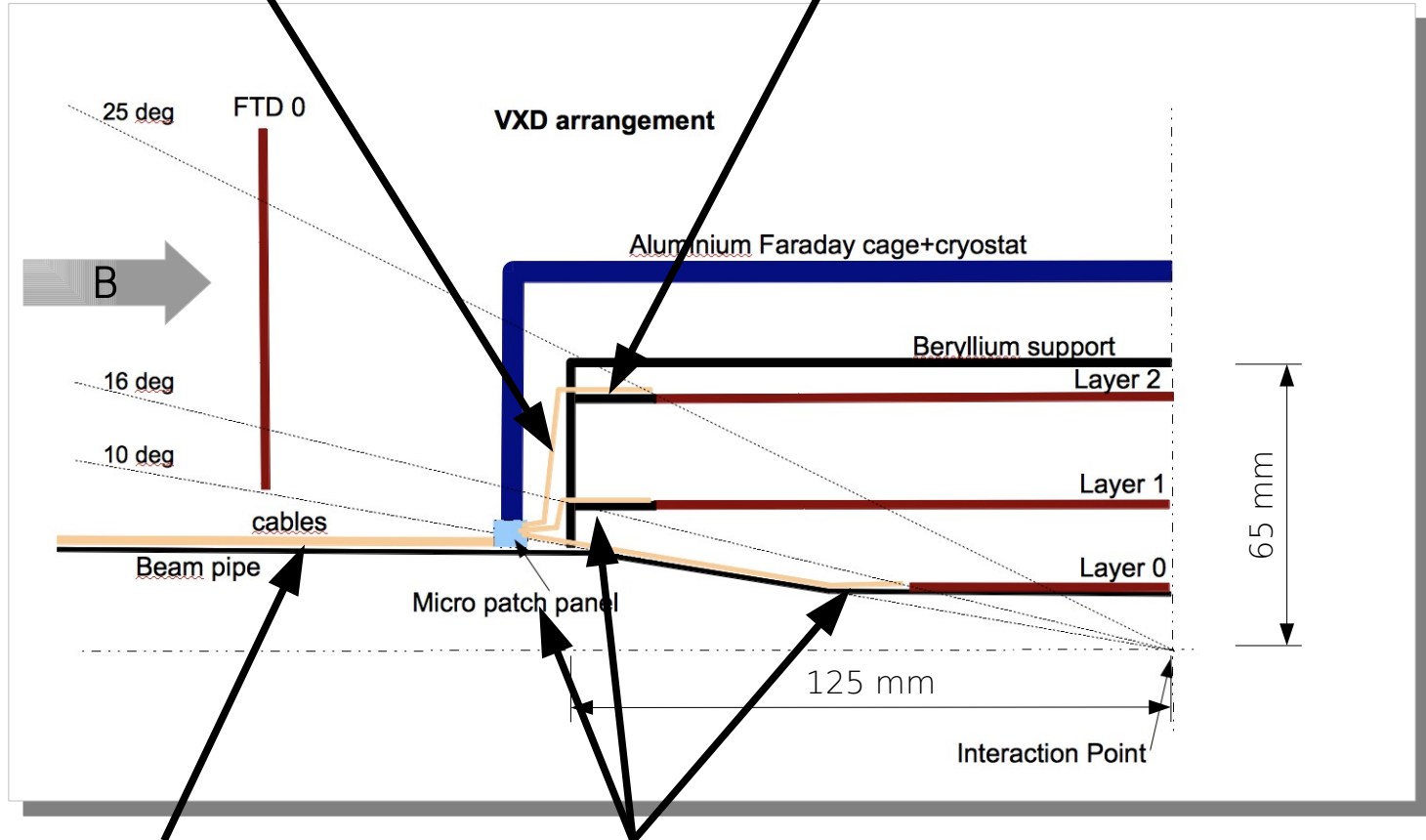
- same concept
- thinner sensor
- thinner cable
- **average $\sim 0.3\%$ X0**

DBD perspective: system 1/3



low-mass cables
+ optic fibers
+ air delivery

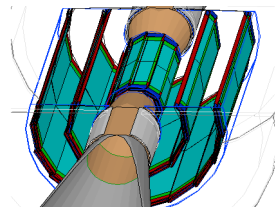
Data concentration + opto-couplers



Model from
CAD tool
& simulation
(except for
air delivery)

copper cables for power
+ optic fibers
+ air pipes

Power re-distribution
& potentially converters



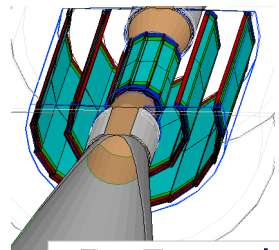
DBD perspective: system 2/3

● Powering

- x Estimation done:
 - Overall dissipation during train (power on) ~ 900 W (0.35 μm techno) \simeq 700 W (0.18 μm techno.)
 - Duty cycle 1/50 to 1/100 → **20 to 30 W in average**
- x Delivery strategy to be optimized:
 - Cable size for 700W seems OK / material budget (< 10 g/ cm on pipe)
 - BUT potential gain with DC-DC converters and/or regulators and/or capacitor
 - Location of converters and patch panel not fixed
 - Several scenario to be identified for DBD
- x Sensor-level power delivery studies ongoing @ IPHC
 - Timeline beyond DBD

● Data flow

- x Estimation done:
 - Driven by the first layer with an average rate of 5 part/cm²/bunchX x 10 (security factor x fluctuation)
 - During train: **$\mathcal{O}(1)$ Tbps data throughput within 1 ms**
- x Optimization with serializer & opto-converter
 - Work in collaboration with SMU-Dallas (ATLAS)
 - Will not converge for DBD



DBD perspective: system 3/3

● Faraday cage & cryostat

- x Current model extrapolated from SLD
- x No recent work...
 - Option to share with first FTD stations ?
- x Potential tests with PLUME ladders but not scheduled yet

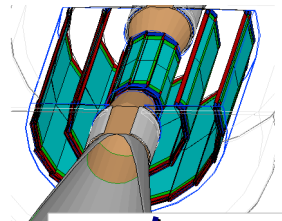
● Mechanical support

- x Current Beryllium support model extrapolated from SLD
- x No changes expected within 12 months

● Cooling

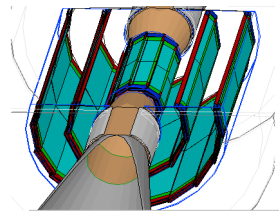
- x Air cooling "seems" sufficient for 20 to 30 W but which air speed?
- x Study for 1 ladder will be completed within PLUME
- x Simulation for whole detector possible @ DESY
- x No work on the air delivery pipe yet

Beyond the DBD



● \sqrt{s} 0.5 \rightarrow 1 TeV

- x Effects: beam bckd x2, physics $\times\sqrt{s}$, longer decay distances
- x Impacts:
 - \rightarrow Sensors with shorter integration time
 - \rightarrow Geometry may be revisited

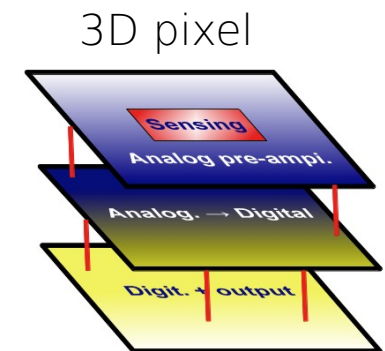


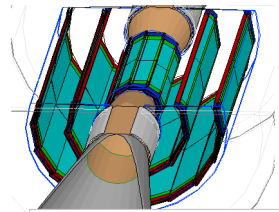
2D CMOS 0.18 μm technology upgrade

- x Lower power or higher speed (20 to 30%)
- x Also: higher data reduction, smaller pitch, higher radiation tolerance, smaller size peripheral circuitry, stitching
- x First prototype to submit in Q4 2011
 - 4-5 years program to reach "final" sensors

3D integration technology

- x Optimizes CMOS techno. for each functionality / tier
- x Very high expectations: $O(10)$ μm pitch with $O(1)$ μs readout or 50 ns time-stamping
- x First prototypes fabricated within consortium coordinated by FNAL
 - Long term program



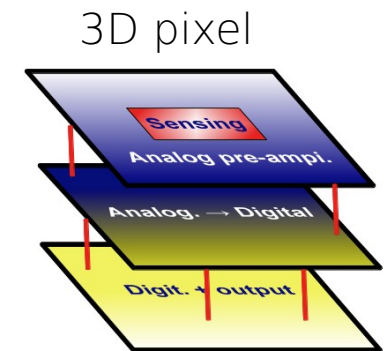


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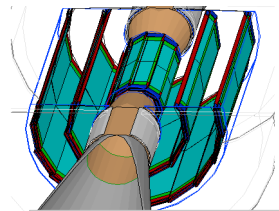
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Ladders

- x Further decrease mat. budget
 - Stitching, embedded sensors
- x single-sided ladders
- x cooling/support alternatives

Beyond the DBD

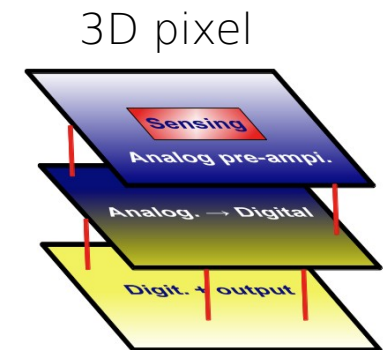


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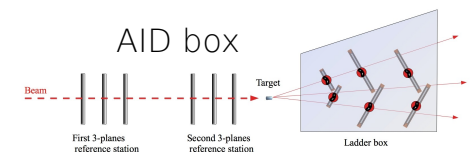


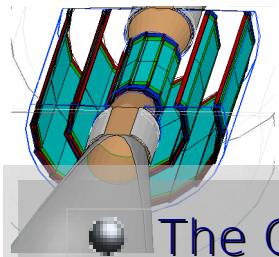
Ladders

- x Further decrease mat. Budget
 - Stitching, embedded sensors
- x single-sided ladders
- x cooling/support alternatives

Algorithm studies

- x Validated on tbeam within AIDA project & PLUME collab.
- x Benefits of 2-sided ladders
 - Alignment, track matching





● The CMOS sensor VXD concept

x 2 sensor flavors

→ inner layers: $\sigma_{s.p.} < 3\mu\text{m}$ for 40 /10 μs integration

→ outer layer: $\sigma_{s.p.} < 4\mu\text{m}$ for 100 μs integration

x Based on well established MIMOSA 26 architecture

● Toward the DBD

x Prototypes for the 2 sensor flavors **fabricated & tested** (beam)

x Double-sided ladder with material budget of 0.6% X0 in 2011 ↘ **0.3 to 0.45 % X0 in 2012 fabricated & tested** (beam)

x Detailed needs estimated for services

● Beyond the DBD

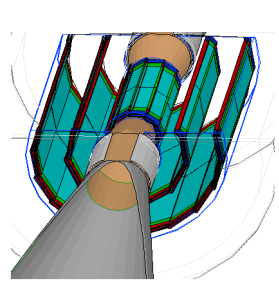
x Technology migration for enhanced performances (2D short-term, 3D long-term)

→ Mitigate integration difficulty (material budget, power)

→ Answer 1 TeV challenges

x Development of services

x Benefits expected from synergy with other projects: STAR, CBM, ALICE, AIDA
→ sensor stitching, readout speed, material budget, integration techniques



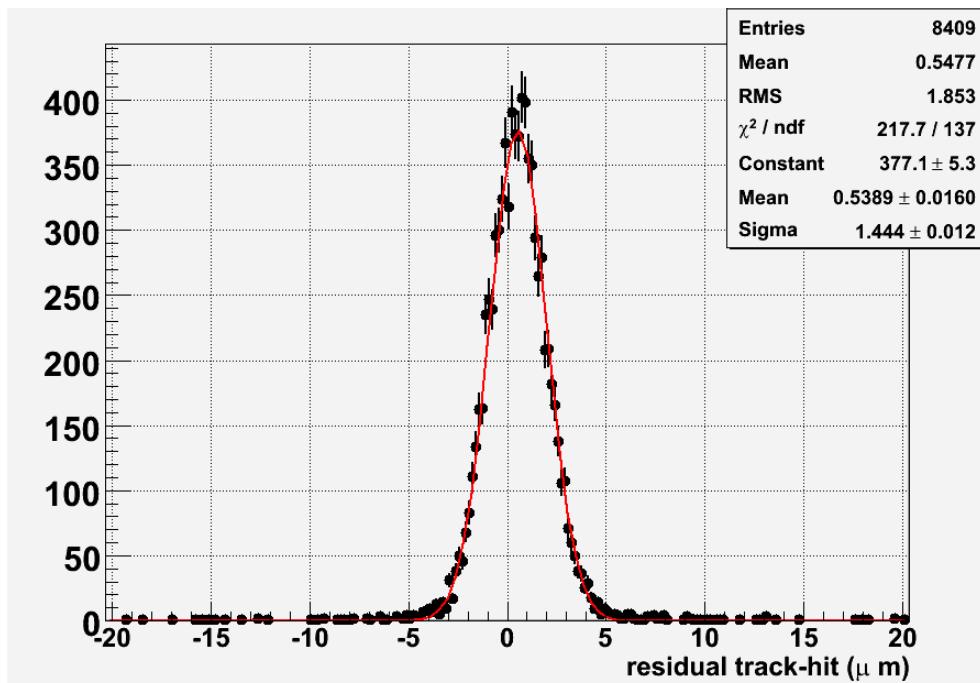
● Additional slides

- x Computing the spatial resolution
- x DEPFET status
- x Pixelated SiT
- x Power pulsing
- x Power & low mass cables
- x Parameter space for VXD

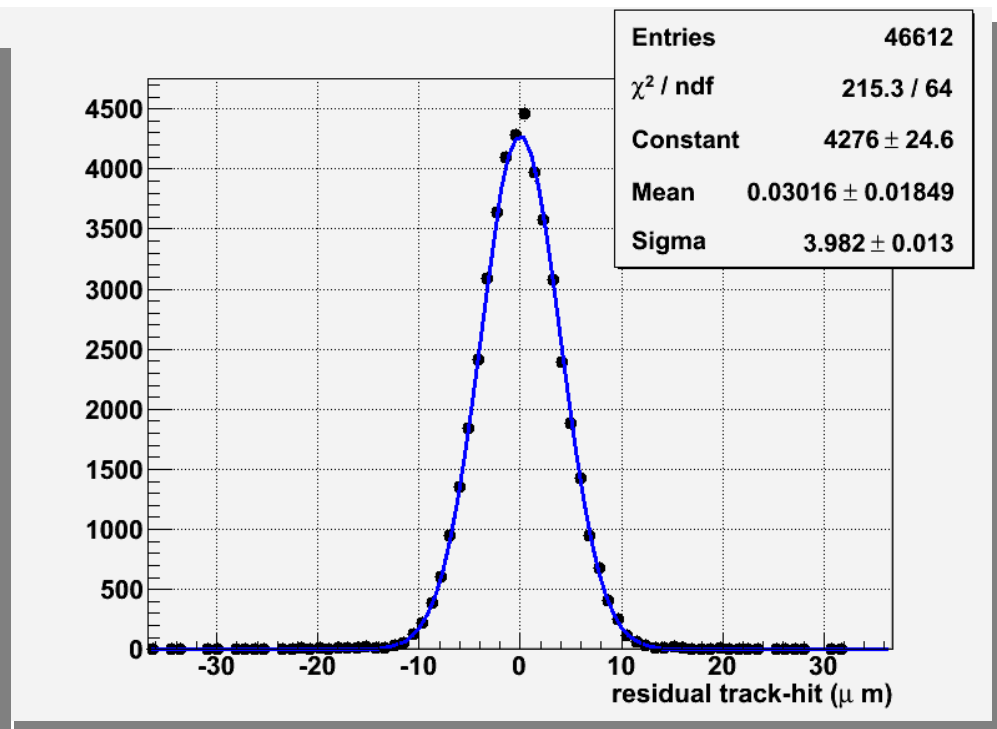
Defining the spatial resolution

From the residual resolution

- x Fit with a single gaussian
- x Spatial resolution = single gaussian std. deviation

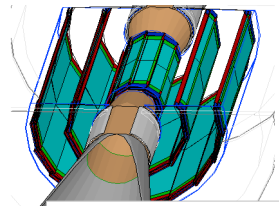


Analog sensor case:
MIMOSA 18, pitch 10 μm



Binary sensor case:
MIMOSA 26, pitch 18.4 μm

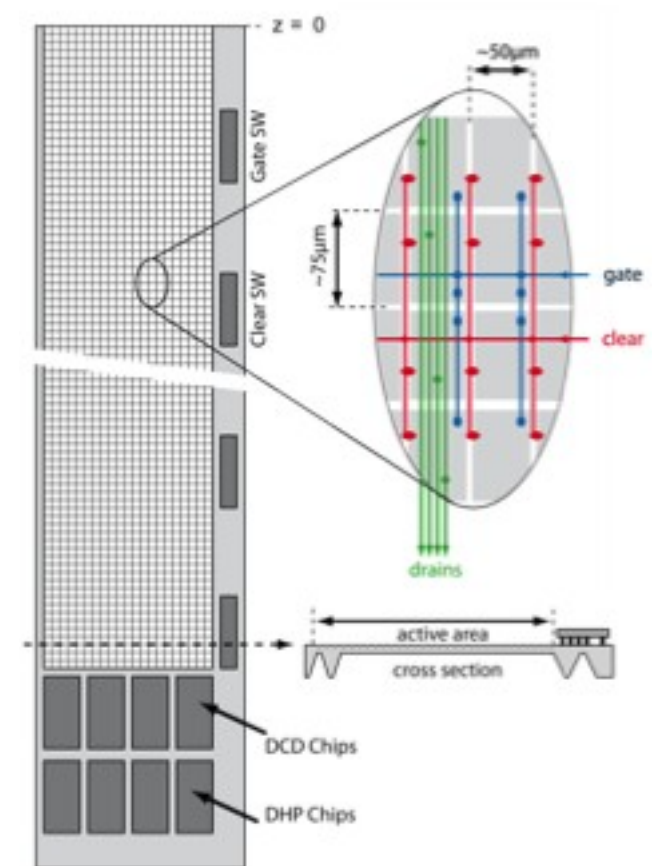
The DEPFET-based VXD



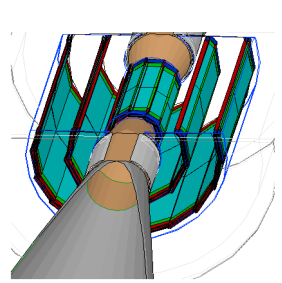
● The Belle II VXD as ILD demonstrator

- x 2 single-sided ladders with DEPFET APS ladders
- x L1: radius 14 mm, $90 \times 12.5 \text{ mm}^2$, 8 ladders, $50 \times 50 \mu\text{m}^2$, 1600x250 pix/ladder
- x L2: radius 22 mm, $126 \times 12.5 \text{ mm}^2$, 12 ladders, $50 \times 75 \mu\text{m}^2$, 1600x250 pix/ladder
- x Thin ($50 \mu\text{m}$) sensitive area, ladder concept like in ILD
 - 0.19 % X0 in fiducial volume
- x Frame rate 100kHz (L1) and 50kHz(L2), continuous read-out
- x Line rate: 12.5 MHz, "rolling shutter" mode
- x Power dissipation per ladder (20 ladders)
 - Sensor $\sim 1 \text{ W}$ + switcher $\sim 1 \text{ W}$
 - DCD+DHP chips $\sim 8 \text{ W}$
- x Radiation damage: a few Mrad/year
- x No requirements in forward region relaxed end-of-ladder (EOL) specs for material and services
- x no power pulsing possible, but aggressive (liquid) cooling on EOL allowed
- x first Belle II data expected 2014

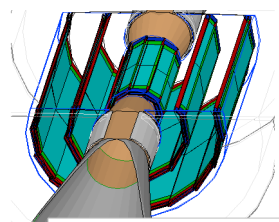
From L.Andricek, 2010



the pixelated SiT option

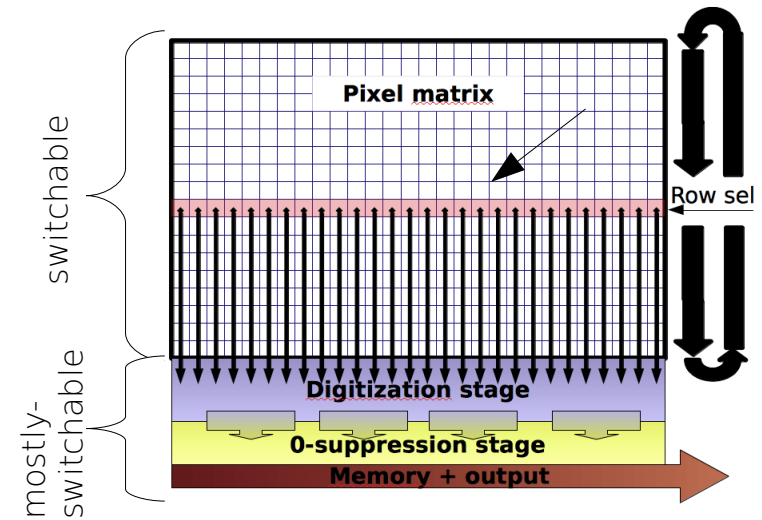


Power pulsing sensor



Pulsing strategy

- x Activity period ~ 2 to 4 ms over the 200 ms train
 - Estimated duty cycle range: 1/50 to 1/100
- x For stability reasons, not all element switchable
 - Test started for the analog part
 - To be done for the digital circuitry



Assuming: 0.18μm techno. & 1.8 V voltage & continuous operation		sensor			2-sided ladder			whole detector		
		switch.	not-swi.	total	switch.	not-swi.	total	switch.	not-swi.	total
inner layer	power (W)	1,575	0,025	1,6	18,9	0,3	19,2	688 W	12 W	700 W
	current (A)	0,875	0,014	0,89	10,5	0,17	10,67			
outer Layers	power (W)	0,490	0,010	0,5	5,88	0,12	6	382 A	7 A	390 A
	current (A)	0,272	0,006	0,28	3,27	0,07	3,33			

Average power (integrating pulsing) 20 to 30 W

→ Air cooling probably good enough

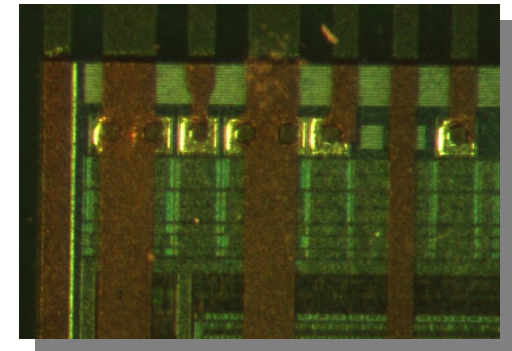
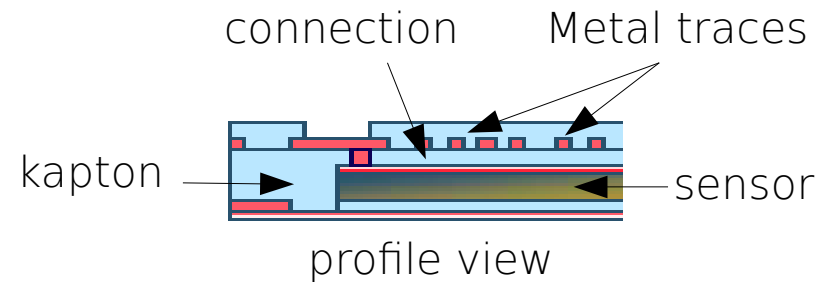
Power pulsing & low mass cables

● Wire bonds

- x Average current through powering wires ~ 10 mA
 - Small residual force in $B=4T$ but vibrations possible
- x Monolithic sensors are easy to handle
 - Possibility to embed in polyimide & connect through metallization
 - IMEC+CMST & CERN projects

● Lorentz force on low mass cable

- x Many "small" transverse traces
 - Residual force could reach few g \approx cable mass!
- x Double-sided structure could be used to counter-balance the effect
 - Cable design with reverse current path on each side
- x Switching sensors with some delay and not simultaneously → reduce current
 - Require specific sensor functionalities



Parameter space for a VXD

